Form PTO-1449 U.S. DEPARTMENT OF COMMERCE (REV. 7-80)PATENT AND TRADEMARK OFFICE				Atty. Docket No. YOR920010308US2 (1	Serial No. 10/775, 515 Unassigned		
LIST OF PRIOR ART CITED BY APPLICANT  (Use several sheets if necessary)				Applicant Jack O. Chu, et al.			
				Filing Date Herewith		Group Unassigned 2818	
U.S. PATI	ENT E	OCUMENTS		•			
EXAMINER INITIAL®		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FIUNG DATE (if appropriate)
PD	AA	5,906,680	5/25/1999	Meyerson			
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PD		6,306,211	10/2001	Takahashi et al.			
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FOREIGN	I PAT	ENT DOCUMENTS	<u></u>				
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OTHER PR	JOR A	ART (Including Author,	Title, Date, Perti	nent Pages, Etc.)			
PD		E. Kasper, et al. "Growth of 100 Ghz SiGe-Heterobiploar Transistor (HBT) Structures," Jpn J App Phys, Vol. 33 Pt. 1, No. 4B, April 1994, pp. 2415-2418;					
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PHUCT. DAMG				DATE CONSIDERED 10/8/2004			
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